

# Radar Pulsed Power Transistor 0.85W, 1.2-1.4 GHz, 2ms Pulse, 20% Duty

M/A-COM Products Released, 30 May 07

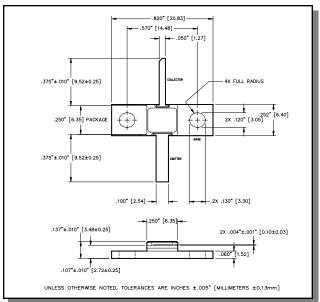
#### **Features**

- NPN silicon microwave power transistors
- Common emitter configuration
- Broadband Class A operation
- · High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- · Hermetic metal/ceramic package
- RoHS compliant

# Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	27	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter-Base Voltage	$V_{EBO}$	3.5	V
Collector Current (Peak)	I <sub>C</sub>	0.71	Α
Power Dissipation @ +25°C	P <sub>TOT</sub>	9.2	W
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## **Outline Drawing**



### Electrical Specifications: T<sub>C</sub> = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 4mA		BV <sub>CES</sub>	27	-	V
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA		BV <sub>CEO</sub>	20	=	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 15V		I <sub>CES</sub>	=	1.0	mA
Thermal Resistance	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	R <sub>TH(JC)</sub>	-	19.0	°C/W
Output Power	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	P <sub>OUT</sub>	0.85	-	W
Power Gain	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	$G_{P}$	9.3	-	dB
Collector Efficiency	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	ης	30	-	%
Input Return Loss	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	2:1	-
Load Mismatch Stability	Vcc = 11.5V, Pin = 0.1W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

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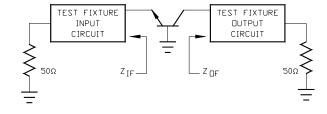
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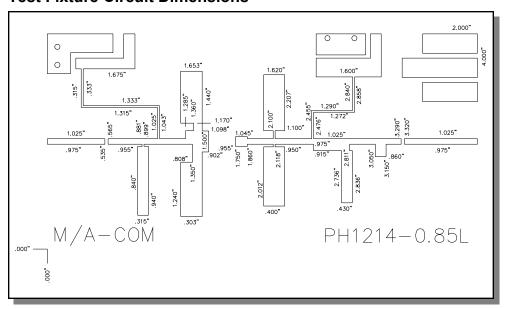
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# **RF Test Fixture Impedance**

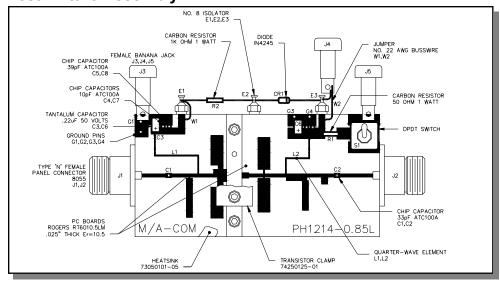
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
1.2	5.9 - j4.5	7.4 + j6.3
1.3	6.4 - j4.0	7.5 + j7.7
1.4	7.1 - j4.4	7.4 + j8.9



#### **Test Fixture Circuit Dimensions**



### **Test Fixture Assembly**



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